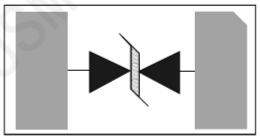
Features

- 60Watts peak pulse power(tp=8/20μs)
- Tiny DFN1006 package
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance(Cj=0.4pFtyp.IO to IO)
- Protection one data/power line
- IEC 61000-4-2±20kV contact ±20kV air
- IEC 61000-4-4(EFT)40A(5/50ns)
- IEC 61000-4-5(Lightning)3.5A(8/20μs)





DFN1006

Applications

- Cell Phone Handsets and Accessories
- Microprocessor based equipment
- Personal Digital Assistants(PDA’ s)
- Notebooks,Desktops,and Servers
- Portable Instrumentation

Mechanical Data

- DFN1006 package
- Packaging:Tape and Reel
- RoHS/WEEE Compliant

Absolute Maximum Rating

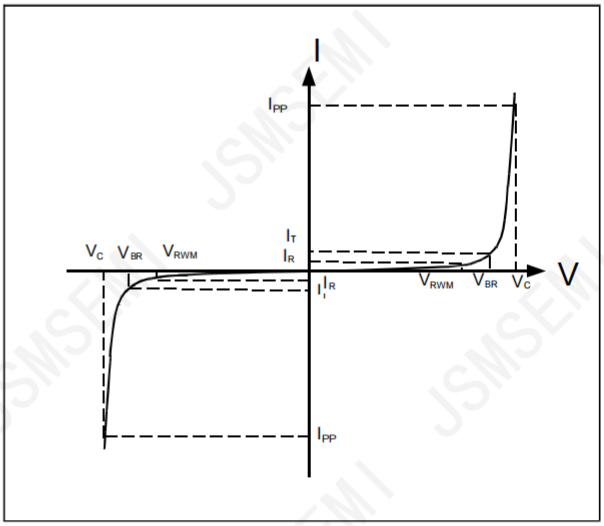
Rating	Symbol	Value	Units
Peak Pulse Power(t_p=8/20μs)	P_{PP}	60	Watts
Peak Pulse Current(t_p=8/20μs)(note1)	I_{pp}	3.5	A
ESD per IEC 61000-4-2(Air) ESD per IEC 61000-4-2(Contact)	V_{ESD}	2020	kV
Lead Soldering Temperature	T_L	260(10seconds)	℃
Junction Temperature	T_J	-55 to+125	℃
Storage Temperature	T_{stg}	-55 to+125	℃

Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{RWM}				5.0	V
Reverse Breakdown Voltage	V_{BR}	I_T=1mA	6.0	8.0		V
Reverse Leakage Current	I_R	V_{RWM}=5V,T=25℃		0.1	0.5	μA
Peak Pulse Current	I_{PP}	tp=8/20μs			3.5	A
Clamping Voltage	V_C	I_{PP}=3.5A,t_p=8/20μs		16	20	V
Junction Capacitance	C_j	IO to IO V_R=0V,f=1MHz		0.4	0.5	pF

Electrical Parameters (TA = 25°C unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage@I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current@V_{RWM}
V_{BR}	Breakdown Voltage@I_T
I_T	Test Current



Note:.8/20μs pulse waveform.

Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

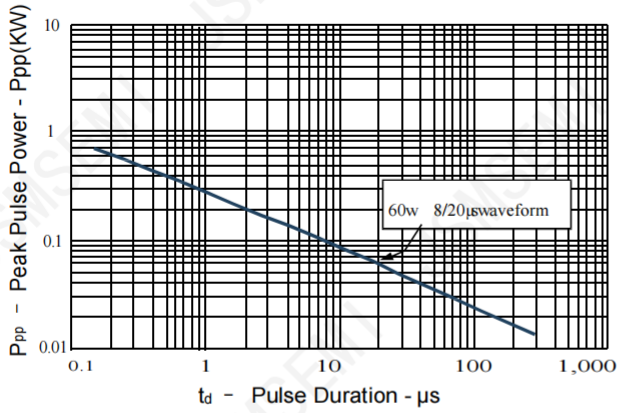


Figure 2: Power Derating Curve

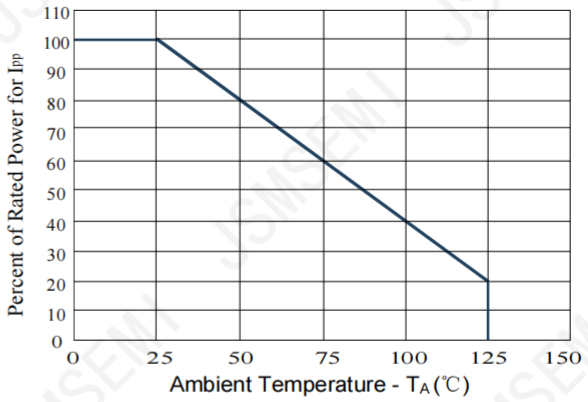


Figure3: Pulse Waveform

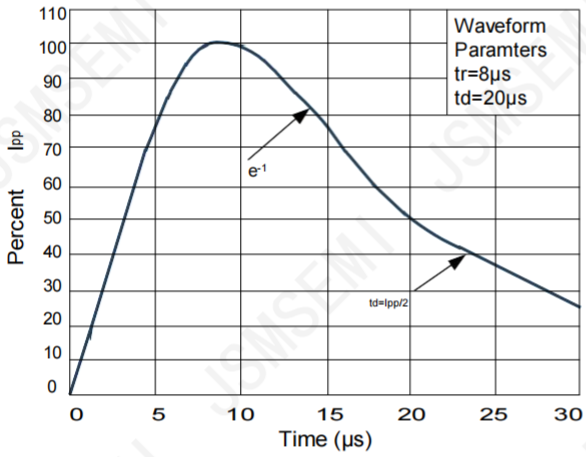


Figure 4: Clamping Voltage vs.Ipp

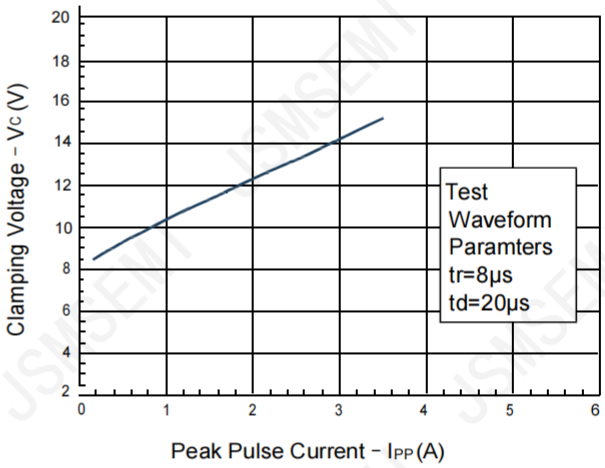


Figure5: Positive Clamping voltage (TLP)

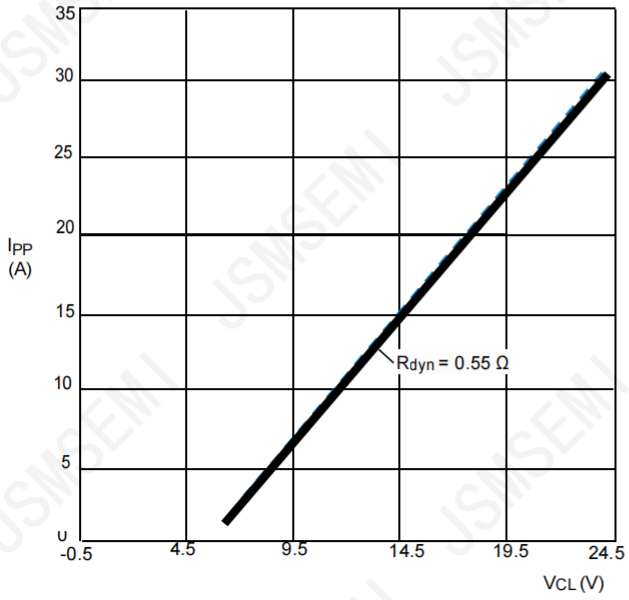
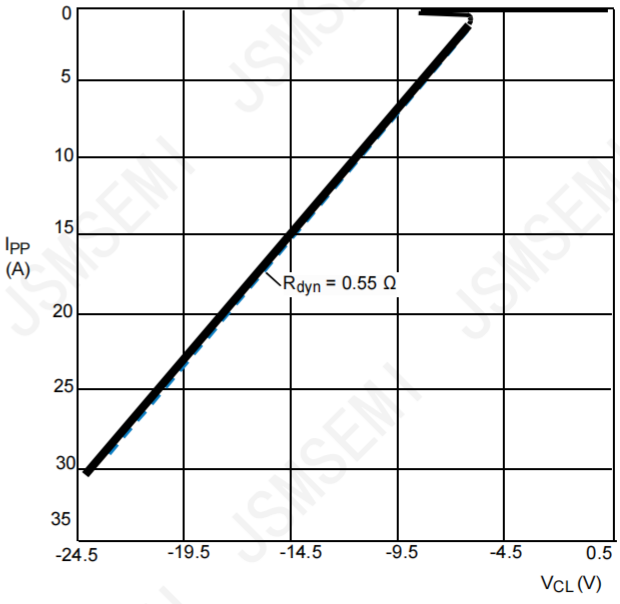
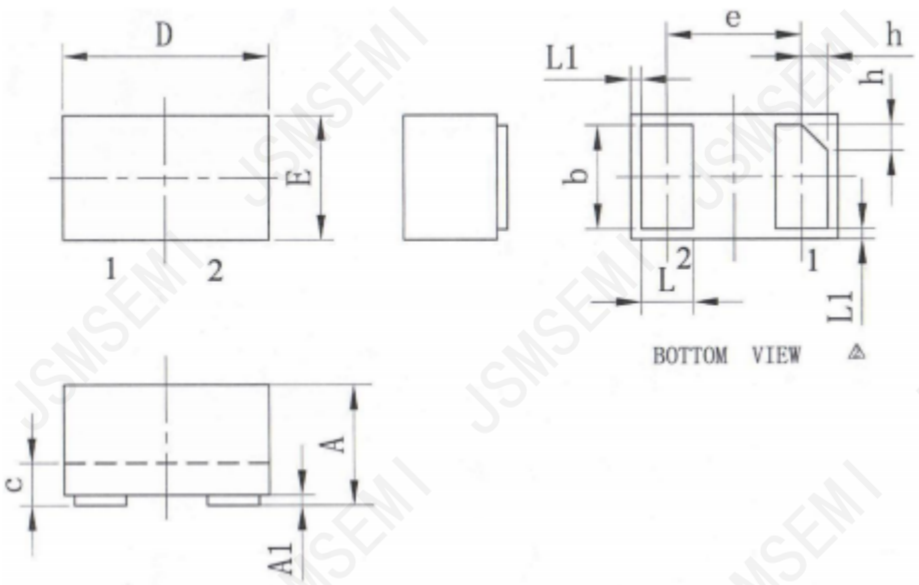


Figure5: Negative Clamping voltage (TLP)



Outline Drawing – DFN1006



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.45	0.50	0.55
A1	0	0.02	0.05
b	0.45	0.50	0.55
c	0.12	0.15	0.18
D	0.95	1.00	1.05
e	0.65BSC		
E	0.55	0.60	0.65
L	0.20	0.25	0.30
L1	0.05REF		
h	0.07	0.12	0.17
载体尺寸 (MIL)	20*20		

Revision History

Rev.	Change	Date
V1.0	Initial version	2/23/2024

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